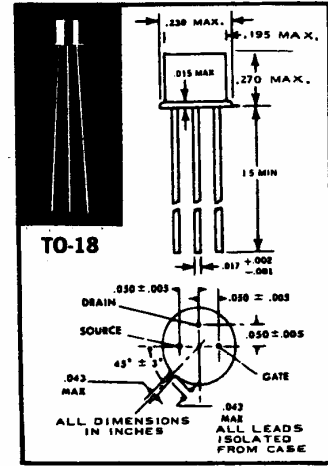
	FOTOFET™ SILICON EPITAXIAL JUNCTION N-CHANNEL FIELD EFFECT TRANSISTOR	FF413
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GEOMETRY 446

- HIGH SENSITIVITY
- LOW DARK CURRENT
- FAST RESPONSE
- LOW R_{ON}
- FLAT GLASS TOP FOR EXTERNAL OPTICS

ELECTRICAL DATA ABSOLUTE MAXIMUM RATING

Drain to Source Voltage	BV_{DSO}	30 Volts
Drain to Gate Voltage	BV_{DGO}	30 Volts
Gate to Source Voltage	BV_{GSO}	-15 Volts
D.C. Forward Gate Current	I_{GF}	50 mA
Junction Temp (operating and storage)	T_J	-65°C to +200°C
Power Dissipation (free air)	P_D	300mW
Lead Temp (@1/16" ± 1/32" from case)	T_L	240°C for 10 sec.
Derating Factor From 200°C	D_F	1.7mW/°C



ACTIVE AREA 0.0009 SQ. CM.
 AT DIE SURFACE SENSITIVITY = .3μA/μW

ELECTRICAL CHARACTERISTICS: $T_A = 25^\circ\text{C}$

PARAMETER	SYMBOL	CONDITION	FF413			Units
			Min.	Typ.	Max.	
Gate Sensitivity ⁵	S_G	$V_{DS} = 15V, V_{GS} = 0, \lambda = .9 \text{ microns}$	1.0	2.0	3.0	$\mu\text{A}/\text{mW}/\text{cm}^2$
Gate Current (Light) ¹	λI_g	$V_{DS} = 15V, V_{GS} = 0V$	2.5	5.0	7.5	nA/FC
Drain Sensitivity ⁴	S_D	$V_{DS} = 15V, I_D = 5\text{mA}, R_G = 1M\Omega$	—	30	—	$\text{mA}/\text{mW}/\text{cm}^2$
Drain Current (Light) ¹	λI_D	$V_{DS} = 15V, I_D = 5\text{mA}, R_G = 1M\Omega$	—	75	—	$\mu\text{A}/\text{FC}$
Zero Gate Voltage Drain Current ⁴	I_{DSS}	$V_{DS} = 15V, V_{GS} = 0$	5.0	35	—	mA
Transconductance	g_m	$V_{DS} = 15V, I_D = 5\text{mA}, f = 1\text{kHz}$	8,000	15,000	25,000	μmho
Rise Time ²	T_R	$V_{DS} = 15V, R_L = 1K, R_G = 1K$	—	25	—	nsec
Fall Time ³	T_F	$V_{DS} = 15V, R_L = 1K, R_G = 1K$	—	40	—	nsec
Pinch-Off Voltage	V_{PO}	$V_{DS} = 25V, I_{DS} = 10.0 \text{ nA}$	1.0	3.0	5.0	Volts
Gate to Source Cap.	C_{GS}	$V_{GS} = -10V, f = 140 \text{ kHz}$	—	—	6.5	pf
Gate to Drain Cap.	C_{GD}	$V_{GD} = -10V, f = 140 \text{ kHz}$	—	—	6.5	pf
Gate Leakage Current (Dark)	I_{GSS}	$V_{GS} = -5V, V_{DS} = 25$	—	0.05	1.0	nA
ON Resistance	R_{DS}	$V_{DS} = 0.1V, V_{GS} = 0$	—	50	100	Ohms

¹ Tungsten Lamp 2800° k Color Temp.

² GAAs Diode Source.

³ Directly Proportional to R_G .

⁴ Pulse Measurement 1% Duty Cycle, 10MS Max.

⁵ Gate Current per unit Radiant Power Density at Lens Surface

⁶ Drain Current per unit Radiant Power Density ($\lambda = 0.9 \text{ microns}$)

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